

Peter Lagov

List of Publications by Year in descending order

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26
papers

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citations

840776

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26
all docs

26
docs citations

26
times ranked

302
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of structural and optical properties of MAPbBr ₃ monocrystals under fast electron irradiation. Journal of Materials Chemistry C, 2022, 10, 5821-5828.	5.5	11
2	Radiation effect on the polymer-based capacitive relative humidity sensors. Nuclear Engineering and Technology, 2022, , .	2.3	1
3	Laser ion source for semiconductor applications. Journal of Physics: Conference Series, 2022, 2244, 012096.	0.4	2
4	Point defect creation by proton and carbon irradiation of $\hat{\Gamma}$ -Ga ₂ O ₃ . Journal of Applied Physics, 2022, 132, .	2.5	11
5	Crystal orientation dependence of deep level spectra in proton irradiated bulk $\hat{\Gamma}$ -Ga ₂ O ₃ . Journal of Applied Physics, 2021, 130, .	2.5	12
6	1â€‰GeV proton damage in $\hat{\Gamma}$ -Ga ₂ O ₃ . Journal of Applied Physics, 2021, 130, .	2.5	7
7	Effect of Electron Irradiation on the Optical Properties of Gadolinium-Aluminum-Gallium Garnet Crystals. Journal of Surface Investigation, 2021, 15, 1259-1263.	0.5	3
8	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. Journal Physics D: Applied Physics, 2020, 53, 445111.	2.8	4
9	Comparison of the Helium Porosity Parameters in Vanadium Alloy TEM Samples Prepared by Various Techniques. Russian Metallurgy (Metally), 2020, 2020, 206-211.	0.5	0
10	Nanosilicon stabilized with ligands: Effect of highâ€‰energy electron beam on luminescent properties. Surface and Interface Analysis, 2020, 52, 957-961.	1.8	4
11	Pulsed fast reactor neutron irradiation effects in Si doped n-type $\hat{\Gamma}$ -Ga ₂ O ₃ . Journal Physics D: Applied Physics, 2020, 53, 274001.	2.8	22
12	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. Journal of Applied Physics, 2019, 126, .	2.5	21
13	Features of Gas Porosity Formation Along Helium Ion Trajectories in Vanadium Alloys. Atomic Energy, 2019, 126, 46-51.	0.4	0
14	Detection of Unreliable Superluminescent Diode Chips Using Gamma-Irradiation. Lecture Notes in Mechanical Engineering, 2019, , 309-317.	0.4	0
15	Development of Gas Porosity along the Ion Range in Vanadium Alloys during Sequential Helium and Hydrogen Ion Irradiation. Russian Metallurgy (Metally), 2019, 2019, 1161-1166.	0.5	1
16	HIGH-RATE HIGH-DENSITY ICP ETCHING OF GERMANIUM. High Temperature Material Processes, 2019, 23, 57-70.	0.6	0
17	Hole traps and persistent photocapacitance in proton irradiated $\hat{\Gamma}$ -Ga ₂ O ₃ films doped with Si. APL Materials, 2018, 6, .	5.1	73
18	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated $\hat{\Gamma}$ -Ga ₂ O ₃ . Applied Physics Letters, 2018, 113, .	3.3	62

#	ARTICLE	IF	CITATIONS
19	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. ECS Journal of Solid State Science and Technology, 2018, 7, P323-P328.	1.8	13
20	Deep Electron and Hole Traps in Electron-Irradiated Green GaN/InGaN Light Emitting Diodes. ECS Journal of Solid State Science and Technology, 2017, 6, Q127-Q131.	1.8	13
21	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. Journal of Applied Physics, 2017, 122, .	2.5	24
22	Electron irradiation of near-UV GaN/InGaN light emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700372.	1.8	11
23	Proton-irradiation technology for high-frequency high-current silicon welding diode manufacturing. Journal of Physics: Conference Series, 2017, 830, 012152.	0.4	3
24	Accelerator-based electron beam technologies for modification of bipolar semiconductor devices. Journal of Physics: Conference Series, 2016, 747, 012085.	0.4	13
25	Magnetic Buncher Accelerator for Radiation Hardness Research and Pulse Detector Characterization. , 2015, , .		6
26	Particularities of Vanadium Microstructure Development During Irradiation by 7.5 MeV Ni ²⁺ Ions at 650Å°C. Atomic Energy, 2015, 118, 400-404.	0.4	2